

SOD-323 Schottky Barrier Diode 肖特基势垒二极管

Internal Configuration & Device Marking 内部结构与产品打标

Type 型号	BAS40WS		
Pin 管脚			
Mark 打标	43		

Absolute Maximum Ratings 最大额定值

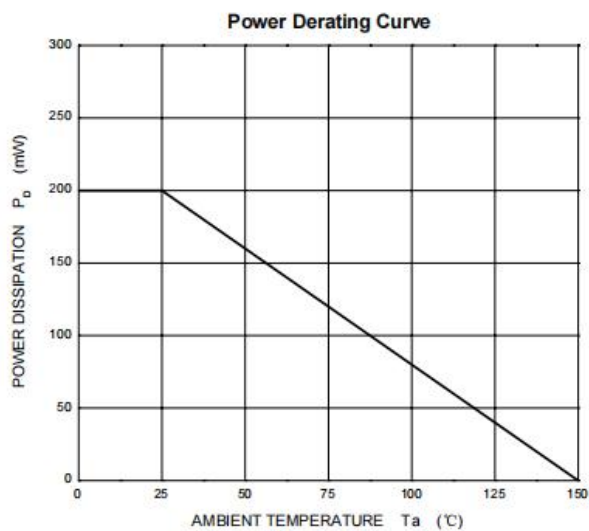
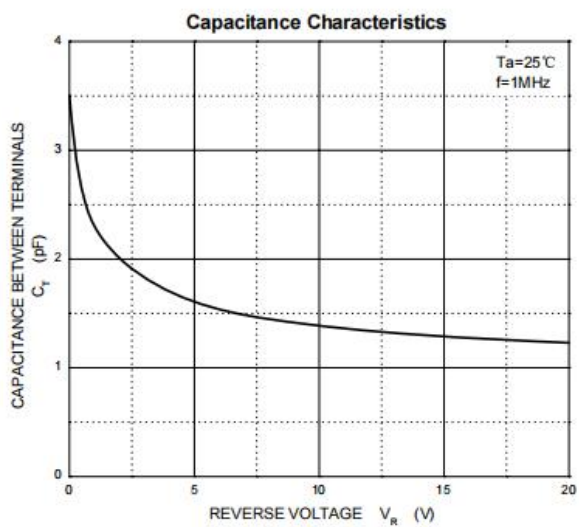
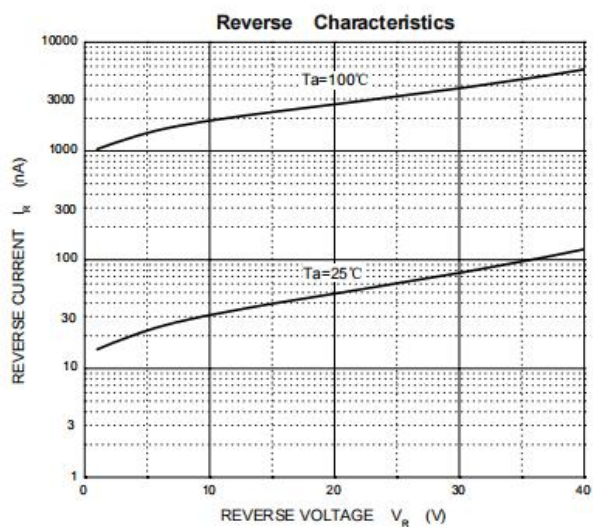
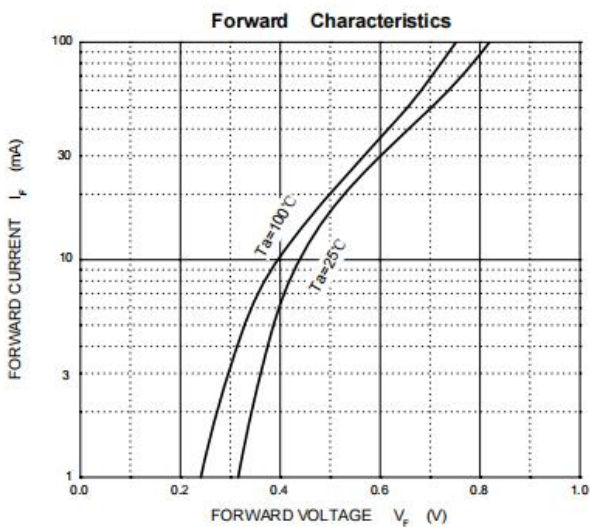
Characteristic 特性参数	Symbol 符号	Rat 额定值	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	40	V
Reverse Work Voltage 反向工作电压	V_{RWM}		
DC Reverse Voltage 直流反向电压	V_R		
Forward Work Current 正向工作电流	$I_F(I_O)$	200	mA
Peak Surge Forward Current 正向峰值浪涌电流	I_{FSM}	600	mA
Power dissipation 耗散功率	$P_D(T_a=25^{\circ}C)$	200	mW
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	500	$^{\circ}C/W$
Junction and Storage Temperature 结温和储藏温度	T_J, T_{stg}	-55to+125 $^{\circ}C$	

Electrical Characteristics 电特性

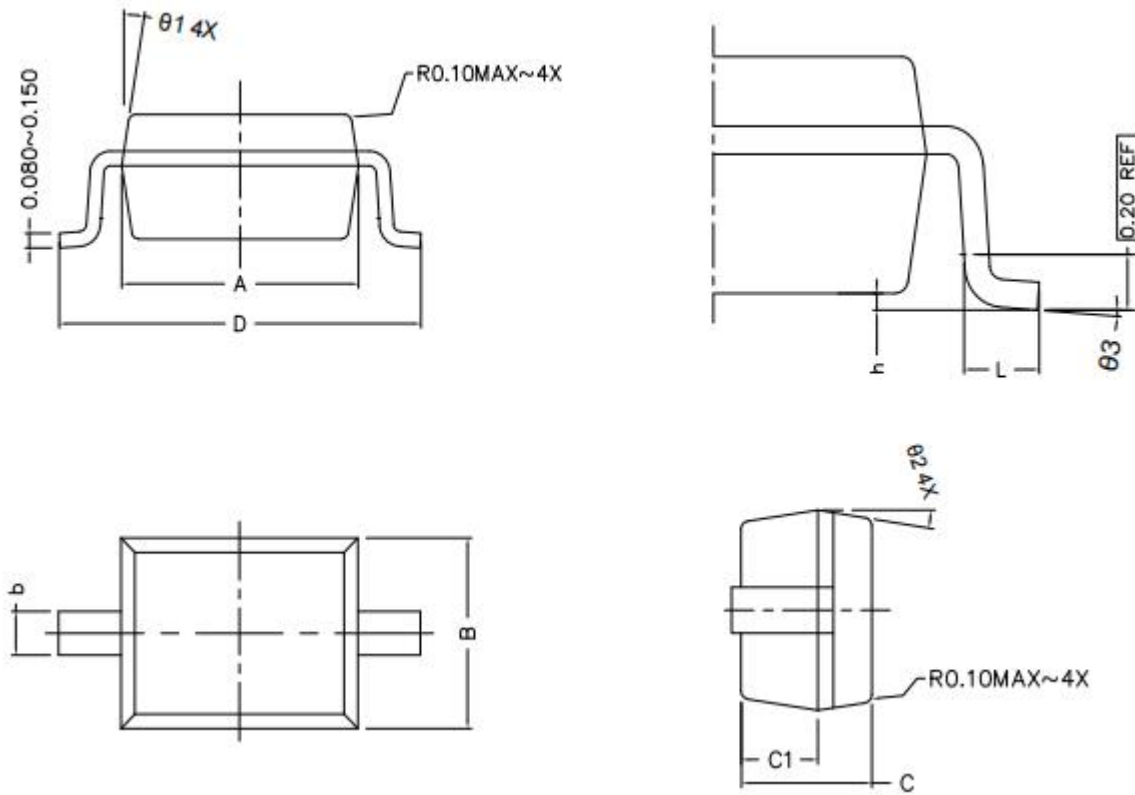
($T_A=25^{\circ}C$ unless otherwise noted 如无特殊说明, 温度为 $25^{\circ}C$)

Characteristic 特性参数	Symbol 符号	Min 最小值	Max 最大值	Unit 单位
Reverse Breakdown Voltage 反向击穿电压($I_R=10\mu A$)	$V_{(BR)}$	40	—	V
Reverse Leakage Current 反向漏电流($V_R=30V$)	I_R	—	0.2	μA
Forward Voltage($I_F=1mA$) 正向电压($I_F=10mA$) ($I_F=40mA$)	V_F		0.38 0.5 1	V
Diode Capacitance 二极管电容($V_R=0V, f=1MHz$)	C_D	—	5	pF
Reverse Recovery Time 反向恢复时间 ($I_F=I_R=10mA, I_{rr}=0.1I_R, R_L=100\Omega$)	T_{rr}	—	5	nS

■ Typical Characteristic Curve 典型特性曲线



■Dimension 外形封装尺寸



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.600	1.800	0.063	0.071
B	1.200	1.400	0.047	0.055
C	0.750	0.950	0.030	0.037
C1	0.450	0.550	0.018	0.022
D	2.450	2.800	0.096	0.110
L	0.200	0.400	0.008	0.016
b	0.200	0.400	0.008	0.016
h	0.020	0.120	0.001	0.005
$\theta 3$	0°	8°	0°	8°